

RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TAN250A** is a Common Base Transistor Designed for DME, TACAN and IFF Pulse Power Amplifier Applications.

FEATURES INCLUDE:

- Gold Metallization
- Hermetic Package
- Input/Output Matching

MAXIMUM RATINGS

I_C	30 A
V_{CB}	60 V
P_{DISS}	575 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
q_{JC}	0.30 °C/W

PACKAGE STYLE		
	MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.890/22.61	.910/23.11
B	.640/16.26	.660/16.76
C	.053/1.35	.073/1.854
D	.115/2.921	.135/3.43
E	.130/3.30	.150/3.81
F	.100/2.54	.120/3.048
G	.395/10.03	.415/10.54
H	.052/1.321	.072/1.829
I	.440/11.18	.460/11.68
J	.376/9.550	.396/10.06
K	.183/4.65	.203/5.156
L		.170/4.318
M		.230/5.842
N	.395/10.03	.407/10.34
O	.003/0.0762	.006/0.152
P	.118/2.997	.131/3.327
Q	.050/1.27	

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 20 mA	60			V
BV_{CES}	I _C = 25 mA R _{BE} = 10 Ω	60			V
BV_{EBO}	I _E = 20 mA	4.0			V
I_{CBO}	V _{CB} = 50 V			12	mA
h_{FE}	V _{CE} = 5 V I _C = 1.0 A	20		120	---
P_{OUT}	V _{CC} = 50 V P _{IN} = 13 W f = 960 to 1215 MHz Pulse Width = 20 μS Duty Cycle = 5 %	250			W
P_G		6.0	7.0		dB
h_C			40		%